



Atty. Dkt. No.	M#	Client Ref.
	309173	P-1583.010-US

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant:	DE SMIT et al.
Appln. No.:	Unknown <u>10/820,217</u>
Filing Date:	April 8, 2004
Examiner:	Unknown
Group Art Unit:	Unknown

Date: May 14, 2004 Page 2 of 3

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
AM	AR 6,600,547	07/2003	WATSON et al.			
	BR 6,603,130	08/2003	BISSCHOPS et al.	250	492.1	
	CR 6,633,365	10/2003	SUENAGA	355	53	
	DR 2002/0163629	11/2002	SWITKES et al.	355	53	
	ER 2003/0123040	07/2003	ALMOGY	355	69	
	FR 2003/0174408	09/2003	ROSTALSKI et al.	359	642	
	GR 2004/0000627 A1	01/2004	SCHUSTER			
	HR 2004/0021844 A1	02/2004	SUENAGA			
AM	IR 2004/0075895 A1	04/2004	LIN	359	380	

FOREIGN PATENT DOCUMENTS

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
AM	JR JP 06-124873	05/1994	JAPAN	TAKAHASHI	X		X	
	KR JP 07-220990	08/1995	JAPAN	FUKUDA et al.	X			
	LR JP 10-228661	08/1998	JAPAN	KUROKAWA	X			
	MR JP 10-255319	09/1998	JAPAN	SUENAGA et al.	X			
	NR JP 10-303114	11/1998	JAPAN	SUWA	X		X	
	OR JP 10-340846	12/1998	JAPAN	KUDO	X		X	
	PR JP 2001-091849	04/2001	JAPAN	AIZAKI et al.	X			
	QR JP 07-132262	05/1995	Japan	HIRAKAWA et al.	X			
	RR JP 58-202448	11/1983	Japan	KAWAMURA et al.	X			
	SR WO2004/019128	03/2004	PCT	OMURA et al.				
	TR WO 03/077037	09/2003	PCT	ROSTALSKI				
AM	UR WO 03/077038	09/2003	PCT	SCHUSTER	X			

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

AM	VR	B.J. LIN, "Drivers, Prospects and Challenges for Immersion Lithography", TSMC, Inc., September 2002			
	WR	B.J. LIN, "Proximity Printing Through Liquid", IBM Technical Disclosure Bulletin, Vol.20, No. 11B, April 1978, p. 4997			
	XR	B.J. LIN, "The Paths To Subhalf-Micrometer Optical Lithography", SPIE Vol. 922, Optical/Laser Microlithography (1988), pp. 256-269			
	YR	G.W.W. STEVENS, "Reduction of Waste Resulting from Mask Defects", Solid State Technology, August 1978, Vol.21 008, pp. 68-72			
	ZR	S. OWA et al., "Immersion Lithography; its potential performance and issues", SPIE Microlithography 2003, 5040-188, February 27, 2003			
AM	AAR	S. OWA et al., "Advantage and Feasibility of Immersion Lithography", Proc. SPIE 5040 (2003)			

Examiner Alan Mathews

Date Considered: 2-18-2006

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.



Atty. Dkt. No.	M#	Client Ref.
	309173	P-1583.010-US

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

Applicant:	DE SMIT et al.
Appn. No.:	Unknown 10/820,227
Filing Date:	April 8, 2004
Examiner:	Unknown
Group Art Unit:	Unknown

Date: May 14, 2004 Page 3 of 3

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
AR						
BR						

FOREIGN PATENT DOCUMENTS

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract	Translation Readily Available
					Enclosed	No
AM	CR DD 206 607	02/1984	GERMANY	WESTPHAL et al.		X
AM	DR DD 221 563	04/1985	GERMANY	PFORR et al.		X
ER						

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

AM	FR	Nikon Precision Europe GmbH, "Investor Relations - Nikon's Real Solutions", May 15, 2003				
	GR	H. KAWATA et al., "Optical Projection Lithography using Lenses with Numerical Apertures Greater than Unity", Microelectronic Engineering 9 (1989), pp. 31-36				
	HR	J.A. HOFFNAGLE et al., "Liquid Immersion Deep-Ultraviolet Interferometric Lithography", J. Vac. Sci. Technol. B., Vol. 17, No. 6, November/December 1999, pp. 3306-3309				
	IR	B.W. SMITH et al., "Immersion Optical Lithography at 193nm", FUTURE FAB International, Vol. 15, July 11, 2003				
	JR	H. KAWATA et al., "Fabrication of 0.2µm Fine Patterns Using Optical Projection Lithography with an Oil Immersion Lens", Jpn. J. Appl. Phys. Vol. 31 (1992), pp. 4174-4177				
	KR	G. OWEN et al., "1/8µm Optical Lithography", J. Vac. Sci. Technol. B., Vol. 10, No. 6, November/December 1992, pp. 3032-3036				
	LR	H. HOGAN, "New Semiconductor Lithography Makes a Splash", PHOTONICS SPECTRA, Photonics TechnologyWorld, October 2003 Edition, pgs. 1-3				
	MR	S. OWA and N. NAGASAKA, "Potential Performance and Feasibility of Immersion Lithography", NGL Workshop 2003, July 10, 2003, Slide Nos. 1-33.				
	NR	S. OWA et al., "Update on 193nm Immersion exposure tool", Litho Forum, International SEMATECH, Los Angeles, January 27-29, 2004, Slide Nos. 1-51				
	OR	H. HATA, "The Development of Immersion Exposure Tools", Litho Forum, International SEMATECH, Los Angeles, January 27-29, 2004, Slide Nos. 1-22				
	PR	T. MATSUYAMA et al., "Nikon Projection Lens Update", SPIE Microlithography 2004, 5377-65, March, 2004				
	QR	"Depth-of-Focus Enhancement Using High Refractive Index Layer on the Imaging Layer", IBM Technical Disclosure Bulletin, Vol. 27, No. 11, April 1985, p. 6521				
✓	RR	A. SUZUKI, "Lithography Advances on Multiple Fronts", EEdesign, EE Times, January 5, 2004				
AM	SR	B. LIN, "The k_3 coefficient in nonparaxial MNA scaling equations for resolution, depth of focus, and Immersion lithography, J. Microlith, Microfab., Microsyst. 1(1):7-12 (2002)				
	TR					

Examiner Alan Mathews

Date Considered: 2-18-2006

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Atty. Dkt. No.	M#	Client Ref.
	309173	P-1583.010-US

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: DE SMIT et al.
Appln. No.: <u>10/820,227</u>
Filing Date: April 8, 2004
Examiner: Unknown Group Art Unit: Unknown

Date: May 14, 2004 Page 1 of 3

U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
AM	AR	3,573,975	04/1971	DHAKA et al.	117	212	
	BR	3,648,587	03/1972	STEVENS	95	44	
	CR	4,348,184	08/1982	TABARELLI et al.	430	311	
	DR	4,396,705	08/1983	AKEYAMA et al.	430	326	
	ER	4,480,910	11/1984	TAKANASHI et al.	355	30	
	FR	5,040,020	08/1991	RAUSCHENBACH et al.	355	53	
	GR	5,121,256	08/1992	CORLE et al.	359	664	
	HR	5,610,683	03/1997	TAKAHASHI	355	53	
	IR	5,715,039	02/1998	FUKUDA et al.	355	53	
	JR	5,825,043	10/1998	SUWA	250	548	
	KR	5,900,354	05/1999	BATCHELDER	430	395	
	LR	6,191,429	02/2001	SUWA	250	548	
AM	MR	6,580,032	05/2003	HATANO	359	656	

FOREIGN PATENT DOCUMENTS

		Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
						Enclosed	No	Enclose	No
AM	NR	EP 0023231	02/1981	EUROPE	TABARELLI et al.	X			
	OR	EP 0418427	03/1991	EUROPE	MIYAKE	X		X	
	PR	EP 1039511	09/2000	EUROPE	MURAKIMI et al.	X		X	
	QR	DD 224448	07/1985	GERMANY	HESSE et al.		X		
	RR	DD 242880	02/1987	GERMANY	KUCH		X		
	SR	FR 2474708	07/1981	FRANCE	LETELLIER		X		
	TR	JP 62-085326	03/1987	JAPAN	MORIUCHI	X			
	UR	JP 62-121417	06/1987	JAPAN	NAKAZAWA	X			
	VR	JP 63-157419	06/1988	JAPAN	NAKASUJI	X			
	WR	JP 04-305915	10/1992	JAPAN	OZEKI et al.	X			
AM	XR	JP 04-305917	10/1992	JAPAN	OZEKI et al.	X			

OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

AM -	YR	EP Search Report for EP 03253694.8 dated March 30, 2004							
	ZR	M. SWITKES et al., "Immersion Lithography at 157 nm", MIT Lincoln Lab, Orlando 2001-1, December 17, 2001							
	AAR	M. SWITKES et al., "Immersion Lithography at 157 nm", J. Vac. Sci. Technol. B., Vol. 19, No. 6, November/December 2001, pp. 2353-2356							
AM -	BBR	M. SWITKES et al., "Immersion Lithography: Optics for the 50 nm Node", 157 Anvers-1, September 4, 2002							

Examiner Alan Mathews

Date Considered: 2-18-2006

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.